

# Switching Diode BAS16M3T5G

## **Features**

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	$V_{R}$	100	Vdc
Peak Forward Current	I <sub>F</sub>	200	mAdc
Peak Forward Surge Current	I <sub>FM(surge)</sub>	500	mAdc

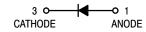
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	260	mW
Derated above 25°C		2.0	mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	490	°C/W
Total Device Dissipation,  FR-4 Board (Note 2)  T <sub>A</sub> = 25°C  Derated above 25°C	P <sub>D</sub>	580 4.6	mW mW/°C
Thermal Resistance,	$R_{\theta JA}$	215	°C/W
Junction-to-Ambient (Note 2)	UJA		-/
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 × 1.0 Inch Pad





## **MARKINGDIAGRAM**



A6 = Specific Device Code M = Date Code

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BAS16M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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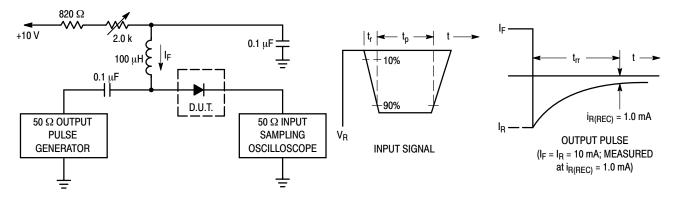
# BAS16M3T5G

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		•
Reverse Voltage Leakage Current $(V_R = 100 \text{ Vdc})$ $(V_R = 75 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ $(V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	I <sub>R</sub>	- - -	1.0 50 30	μAdc
Reverse Breakdown Voltage (I <sub>BR</sub> = 100 μAdc)	V <sub>(BR)</sub>	100	-	Vdc
Forward Voltage $(I_F = 1.0 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 150 \text{ mAdc})$	V <sub>F</sub>	- - -	715 855 1000 1250	mV
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)	C <sub>D</sub>	-	2.0	pF
Forward Recovery Voltage (I <sub>F</sub> = 10 mAdc, t <sub>r</sub> = 20 ns)	V <sub>FR</sub>	-	1.75	Vdc
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, R_L = 50 \Omega)$	t <sub>rr</sub>	-	6.0	ns
Stored Charge (I <sub>F</sub> = 10 mAdc to V <sub>R</sub> = 5.0 Vdc, R <sub>L</sub> = 500 $\Omega$ )	Q <sub>S</sub>	-	45	pC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# BAS16M3T5G



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- 3. t<sub>p</sub> » t<sub>rr</sub>

Figure 1. Recovery Time Equivalent Test Circuit

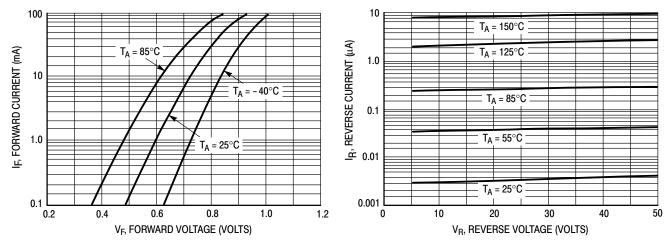


Figure 2. Forward Voltage

Figure 3. Leakage Current

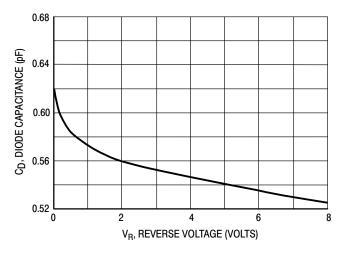


Figure 4. Capacitance





# SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

**DATE 24 JAN 2024** 

MAX.

0.55

0.27

0.37

0.17

1.25

0.85

1.25

MILLIMETERS

 $N\square M$ .

0.50

0.21

0.31

0.12

1.20

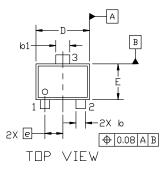
0.80

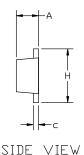
0.40 BSC

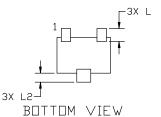
1.20

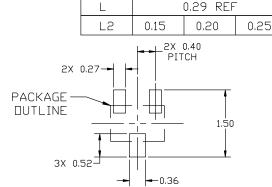
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.









DIM

Α

b

b1

c D

Ε

e H MIN.

0.45

0.15

0.25

0.07

1.15

0.75

1.15

# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

# GENERIC MARKING DIAGRAM\*



XX = Specific Device Code M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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